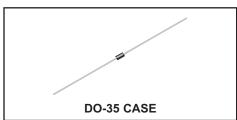
1N5306-20

SILICON CURRENT LIMITING DIODE



SYMBOL

Pov 100 V P_{D} 600 $\, mW \,$ -65 to +200 °C T_J, T_{sta}

MAXIMUM RATINGS: (T_L=75°C) Peak Operating Voltage Power Dissipation

Operating and Storage Junction Temperature

ELECTRICAL CHARACTERISTICS: (T_A=25°C)

Regulator Current (Note 1) Ip @ V _T =25V			Minimum Dynamic Impedance Z _T @ V _T =25V	Minimum Knee Impedance Z _K @ V _K =6.0V	Maximum Limiting Voltage V _L @ I _L =0.8 x I _P MIN
MIN mA	NOM mA	MAX mA	ΜΩ	MΩ	V
1.76	2.20	2.64	0.370	0.052	1.95

Note 1: Pulsed Method: Pulse Width = 12.5ms

DESCRIPTION:

Semiconductor Corp

MARKING CODE: C5306-20

The CENTRAL SEMICONDUCTOR 1N5306-20 is a silicon field effect current regulator diode designed for applications requiring a constant current over a wide voltage range. These devices are manufactured in the cost effective DO-35 double plug case which provides many benefits to the user, including space savings and improved thermal characteristics.

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UNITS

R0 (21-December 2015)

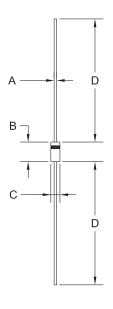
1N5306-20

SILICON CURRENT LIMITING DIODE



DO-35 CASE - MECHANICAL OUTLINE

R1



DIMENSIONS									
	INCHES		MILLIMETERS						
SYMBOL	MIN	MAX	MIN	MAX					
Α	0.018	0.022	0.46	0.56					
В	0.120	0.200	3.05	5.08					
С	0.060	0.090	1.52	2.29					
D	1.000	-	25.40	-					

DO-35 (REV: R1)

MARKING CODE: C5306-20

R0 (21-December 2015)